

IR2151

SELF-OSCILLATING HALF-BRIDGE DRIVER

Features

- Floating channel designed for bootstrap operation
Fully operational to +600V
Tolerant to negative transient voltage
dV/dt immune
- Undervoltage lockout
- Programmable oscillator frequency

$$f = \frac{1}{1.4 \times (R_T + 75\Omega) \times C_T}$$

- Matched propagation delay for both channels
- Low side output in phase with R_T

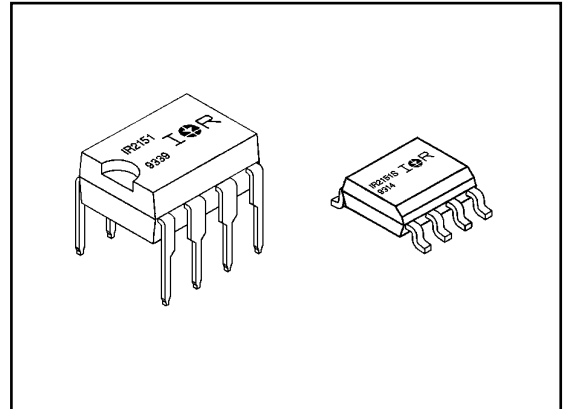
Description

The IR2151 is a high voltage, high speed, self-oscillating power MOSFET and IGBT driver with both high and low side referenced output channels. Proprietary HVIC and latch immune CMOS technologies enable ruggedized monolithic construction. The front end features a programmable oscillator which is similar to the 555 timer. The output drivers feature a high pulse current buffer stage and an internal deadtime designed for minimum driver cross-conduction. Propagation delays for the two channels are matched to simplify use in 50% duty cycle applications. The floating channel can be used to drive an N-channel power MOSFET or IGBT in the high side configuration that operates off a high voltage rail up to 600 volts.

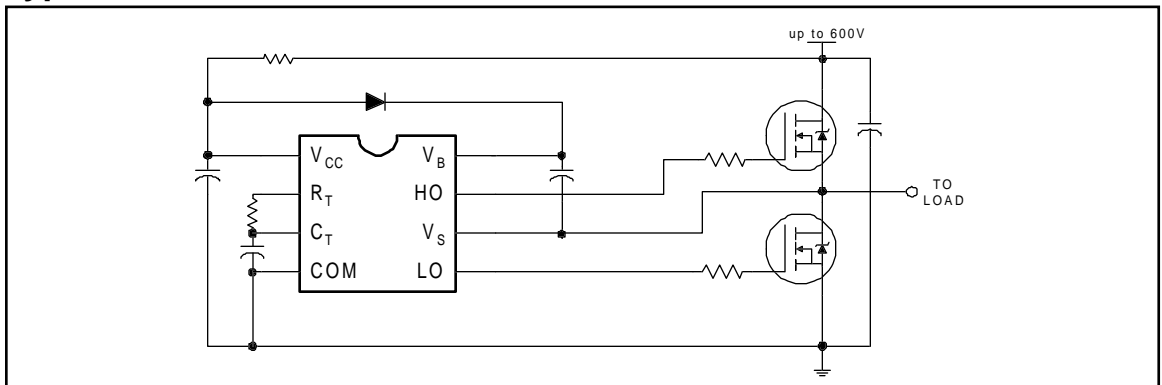
Product Summary

V_{OFFSET}	600V max.
Duty Cycle	50%
I_{o+/-}	100 mA / 210 mA
V_{OUT}	10 - 20V
Deadtime (typ.)	1.2 μs

Packages



Typical Connection



Absolute Maximum Ratings

Absolute Maximum Ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to COM. The Thermal Resistance and Power Dissipation ratings are measured under board mounted and still air conditions.

Symbol	Parameter Definition	Value		Units
		Min.	Max.	
V _B	High Side Floating Supply Voltage	-0.3	625	V
V _S	High Side Floating Supply Offset Voltage	V _B - 25	V _B + 0.3	
V _{HO}	High Side Floating Output Voltage	V _S - 0.3	V _B + 0.3	
V _{LO}	Low Side Output Voltage	-0.3	V _{CC} + 0.3	
V _{RT}	R _T Voltage	-0.3	V _{CC} + 0.3	
V _{CT}	C _T Voltage	-0.3	V _{CC} + 0.3	
I _{CC}	Supply Current (Note 1)	—	25	mA
I _{RT}	R _T Output Current	-5	5	
dV _S /dt	Allowable Offset Supply Voltage Transient	—	50	V/ns
P _D	Package Power Dissipation @ T _A ≤ +25°C (8 Lead DIP)	—	1.0	W
	(8 Lead SOIC)	—	0.625	
R _{θJA}	Thermal Resistance, Junction to Ambient (8 Lead DIP)	—	125	°C/W
	(8 Lead SOIC)	—	200	
T _J	Junction Temperature	—	150	°C
T _S	Storage Temperature	-55	150	
T _L	Lead Temperature (Soldering, 10 seconds)	—	300	

Recommended Operating Conditions

The Input/Output logic timing diagram is shown in Figure 1. For proper operation the device should be used within the recommended conditions. The V_S offset rating is tested with all supplies biased at 15V differential.

Symbol	Parameter Definition	Value		Units
		Min.	Max.	
V _B	High Side Floating Supply Absolute Voltage	V _S + 10	V _S + 20	V
V _S	High Side Floating Supply Offset Voltage	—	600	
V _{HO}	High Side Floating Output Voltage	V _S	V _B	
V _{LO}	Low Side Output Voltage	0	V _{CC}	
I _{CC}	Supply Current (Note 1)	—	5	mA
T _A	Ambient Temperature	-40	125	°C

Note 1: Because of the IR2151's application specificity toward off-line supply systems, this IC contains a zener clamp structure between the chip V_{CC} and COM which has a nominal breakdown voltage of 15.6V. Therefore, the IC supply voltage is normally derived by forcing current into the supply lead (typically by means of a high value resistor connected between the chip V_{CC} and the rectified line voltage and a local decoupling capacitor from V_{CC} to COM) and allowing the internal zener clamp circuit to determine the nominal supply voltage. Therefore, this circuit should not be driven by a DC, low impedance power source of greater than V_{CLAMP}.

Dynamic Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 12V, C_L = 1000 pF and T_A = 25°C unless otherwise specified.

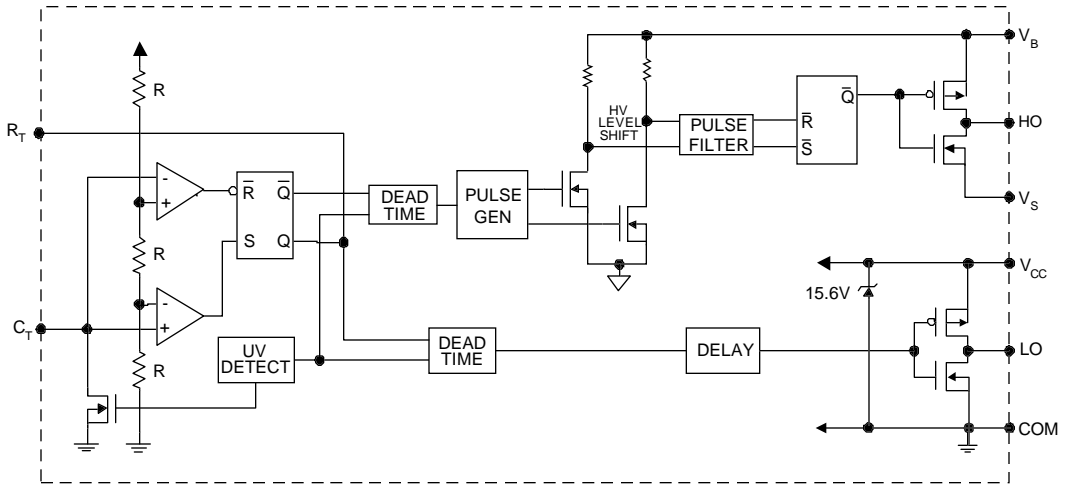
Symbol	Parameter Definition	Value			Units	Test Conditions
		Min.	Typ.	Max.		
t_r	Turn-On Rise Time	—	80	120	ns	
t_f	Turn-Off Fall Time	—	40	70		
DT	Deadtime	0.50	1.20	2.25	μ s	
D	R_T Duty Cycle	48	50	52	%	

Static Electrical Characteristics

V_{BIAS} (V_{CC} , V_{BS}) = 12V, C_L = 1000 pF, C_T = 1 nF and T_A = 25°C unless otherwise specified. The V_{IN} , V_{TH} and I_{IN} parameters are referenced to COM. The V_O and I_O parameters are referenced to COM and are applicable to the respective output leads: HO or LO.

Symbol	Parameter Definition	Value			Units	Test Conditions
		Min.	Typ.	Max.		
f_{OSC}	Oscillator Frequency	19.4	20.0	20.6	kHz	$R_T = 35.7 \text{ k}\Omega$
		94	100	106		$R_T = 7.04 \text{ k}\Omega$
V_{CLAMP}	V_{CC} Zener Shunt Clamp Voltage	14.4	15.6	16.8	V	$I_{CC} = 5 \text{ mA}$
V_{CT+}	2/3 V_{CC} Threshold	7.8	8.0	8.2	V	
V_{CT-}	1/3 V_{CC} Threshold	3.8	4.0	4.2		
V_{CTUV}	C_T Undervoltage Lockout	—	20	50	mV	$2.5V < V_{CC} < V_{CCUV+}$
V_{RT+}	R_T High Level Output Voltage, $V_{CC} - R_T$	—	0	100		$I_{RT} = -100 \mu\text{A}$
		—	200	300		$I_{RT} = -1 \text{ mA}$
V_{RT-}	R_T Low Level Output Voltage	—	20	50		$I_{RT} = 100 \mu\text{A}$
		—	200	300		$I_{RT} = 1 \text{ mA}$
V_{RTUV}	R_T Undervoltage Lockout, $V_{CC} - R_T$	—	0	100		$2.5V < V_{CC} < V_{CCUV+}$
V_{OH}	High Level Output Voltage, $V_{BIAS} - V_O$	—	—	100	V	$I_O = 0\text{A}$
V_{OL}	Low Level Output Voltage, V_O	—	—	100		$I_O = 0\text{A}$
I_{LK}	Offset Supply Leakage Current	—	—	50	μ A	$V_B = V_S = 600\text{V}$
I_{QBS}	Quiescent V_{BS} Supply Current	—	10	50		
I_{QCC}	Quiescent V_{CC} Supply Current	—	400	950		
I_{CT}	C_T Input Current	—	0.001	1.0		
V_{CCUV+}	V_{CC} Supply Undervoltage Positive Going Threshold	7.7	8.4	9.2	V	
V_{CCUV-}	V_{CC} Supply Undervoltage Negative Going Threshold	7.4	8.1	8.9		
V_{CCUVH}	V_{CC} Supply Undervoltage Lockout Hysteresis	200	500	—	mV	
I_{O+}	Output High Short Circuit Pulsed Current	100	125	—	mA	$V_O = 0\text{V}$
I_{O-}	Output Low Short Circuit Pulsed Current	210	250	—		$V_O = 15\text{V}$

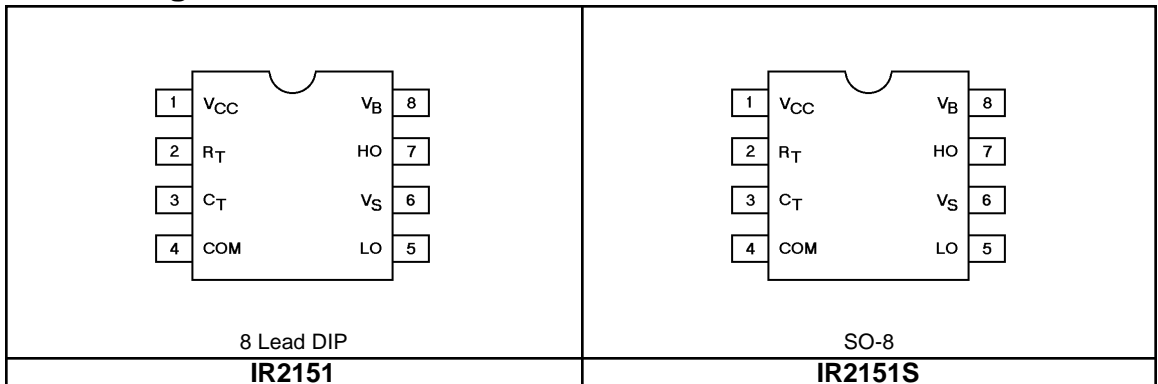
Functional Block Diagram



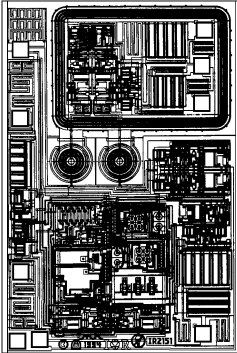
Lead Definitions

Symbol	Description
R_T	Oscillator timing resistor input, in phase with LO for normal IC operation
C_T	Oscillator timing capacitor input, the oscillator frequency according to the following equation: $f = \frac{1}{1.4 \times (R_T + 75\Omega) \times C_T}$ where 75Ω is the effective impedance of the R_T output stage
V_B	High side floating supply
HO	High side gate drive output
V_S	High side floating supply return
V_{CC}	Low side and logic fixed supply
LO	Low side gate drive output
COM	Low side return

Lead Assignments



Device Information

Process & Design Rule		HVDCMOS 4.0 μ m
Transistor Count		231
Die Size		68 X 101 X 26 (mil)
Die Outline		
Thickness of Gate Oxide		800Å
Connections	Material	Poly Silicon
	First Layer	
	Width	5 μ m
	Spacing	6 μ m
	Thickness	5000Å
	Material	Al - Si - Cu (Si: 1.0%, Cu \pm 0.5%)
	Second Layer	
	Width	6 μ m
	Spacing	9 μ m
	Thickness	20,000Å
Contact Hole Dimension		5 μ m X 5 μ m
Insulation Layer	Material	PSG (SiO ₂)
	Thickness	1.7 μ m
Passivation	Material	PSG (SiO ₂)
	Thickness	1.7 μ m
Method of Saw		Full Cut
Method of Die Bond		Ablebond 84 - 1
Wire Bond	Method	Thermo Sonic
	Material	Au (1.0 mil / 1.3 mil)
Leadframe	Material	Cu
	Die Area	Ag
	Lead Plating	Pb : Sn (37 : 63)
Package	Types	8 Lead PDIP / SO-8
	Materials	EME6300 / MP150 / MP190
Remarks:		

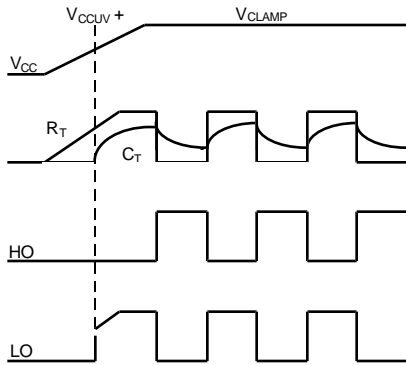


Figure 1. Input/Output Timing Diagram

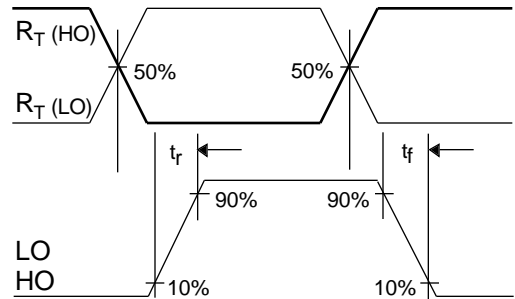


Figure 2. Switching Time Waveform Definitions

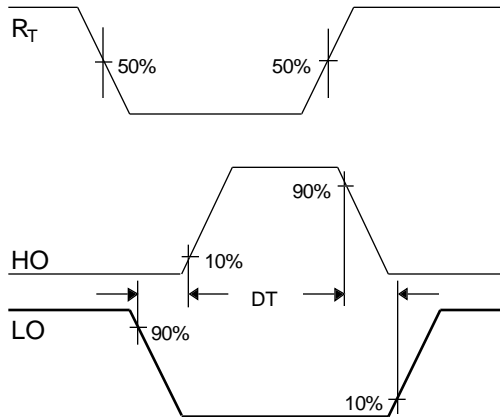


Figure 3. Deadtime Waveform Definitions